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FDA24N50

May 2014

N-Channel UniFETTM MOSFET 500 V, 24 A, 190 m Ω

Features

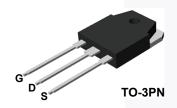
- $R_{DS(on)}$ = 160 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 12 A
- Low Gate Charge (Typ. 65 nC)
- Low C_{rss} (Typ. 35 pF)
- · 100% Avalanche Tested
- · RoHS Compliant

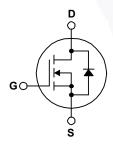
Applications

- PDP TV
- · Uninterruptible Power Supply
- · AC-DC Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





MOSFET Maximum Ratings $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol		Parameter		FDA24N50	Unit
V _{DSS}	Drain to Source Voltage			500	V
V _{GSS}	Gate to Source Voltage			±30	V
	- Continuous ($T_C = 25^{\circ}C$)			24	А
ID	Drain Current	- Continuous (T _C = 100°C)		14	A
I _{DM}	Drain Current	- Pulsed	- Pulsed (Note 1)		Α
E _{AS}	Single Pulsed Avalanche	Energy	(Note 2)	1872	mJ
I _{AR}	Avalanche Current		(Note 1)	24	Α
E _{AR}	Repetitive Avalanche Energy (Note 1)		(Note 1)	27	mJ
dv/dt	Peak Diode Recovery dv	/dt	(Note 3)	4.5	V/ns
D	Dower Discinction	$(T_C = 25^{\circ}C)$		270	W
P_{D}	Power Dissipation	- Derate Above 25°C		2.2	W/°C
T _J , T _{STG}	Operating and Storage T	emperature Range		-55 to +150	°C
TL	Maximum Lead Tempera	ture for Soldering, 1/8" from Case for 5 Sec	conds	300	°C

Thermal Characteristics

Symbol	Parameter	FDA24N50	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.46	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDA24N50	FDA24N50	TO-3PN	Tube	N/A	N/A	30 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	rest Conditions	win.	ıyp.	wax.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_J = 25^{\circ} C$	500	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	-	0.66	-	V/°C
1	Zero Gate Voltage Drain Current	$V_{DS} = 500 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μА
I _{DSS} Zero Gate voltage Drain Current	$V_{DS} = 400 \text{ V}, T_C = 125^{\circ}\text{C}$	-	-	10	μΑ	
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	3.0	-	5.0	V
R _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 12 \text{ A}$	-	0.16	0.19	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = 20 \text{ V}, I_{D} = 12 \text{ A}$	-	28	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 05 V V 0 V		\ -	3120	4150	pF
Coss	Output Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		-	460	615	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 1/11/12		-\	35	52	pF
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 400 V, I _D = 24 A,		- \	65	85	nC
Q_{gs}	Gate to Source Gate Charge	V _{GS} = 10 V		- \	18	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	(No	ote 4)	-	26	-	nC

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-	47	104	ns
t _r		$V_{DD} = 250 \text{ V}, I_D = 24 \text{ A},$	-	108	226	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10 V, R_G = 25 Ω	- /	164	338	ns
t _f	Turn-Off Fall Time	(Note 4)	- /	86	182	ns

Drain-Source Diode Characteristics

Is	Maximum Continuous Drain to Source Diode Forward Current		-/-	-	24	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		A -	-	96	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 24 A	-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 24 A,	-	540	-	ns
Q _{rr}	Reverse Recovery Charge	e Recovery Charge dI _F /dt = 100 A/μs		8.1	-	μC

Notes:

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 6.5 mH, I_{AS} = 24 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C.
- 3. I_{SD} \leq 24 A, di/dt \leq 200 A/µs, V_{DD} \leq BV_DSS, starting T_J = 25°C.
- Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

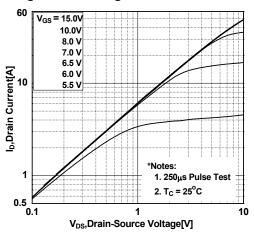


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

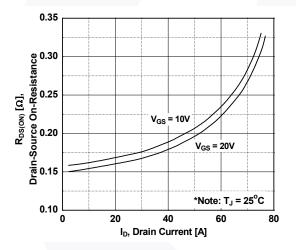


Figure 5. Capacitance Characteristics

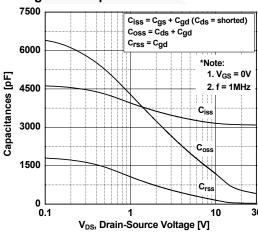


Figure 2. Transfer Characteristics

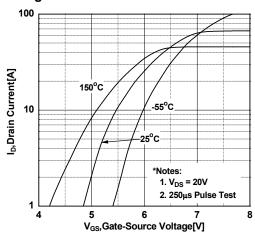


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

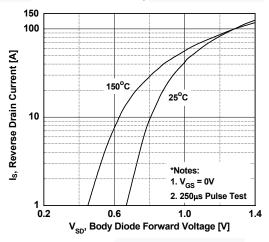
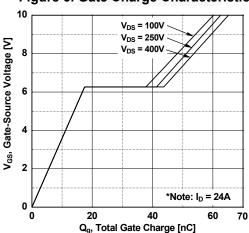


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

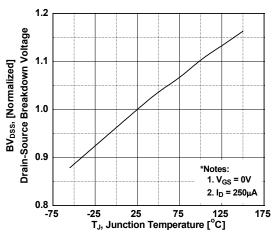


Figure 8. On-Resistance Variation vs. Temperature

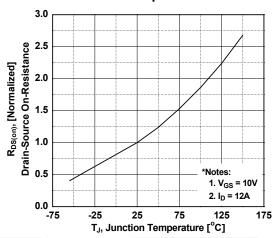


Figure 9. Maximum Safe Operating Area

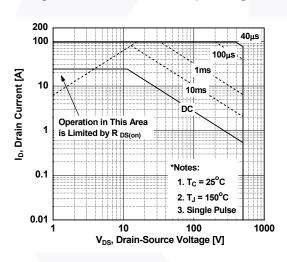


Figure 10. Maximum Drain Current vs. Case Temperature

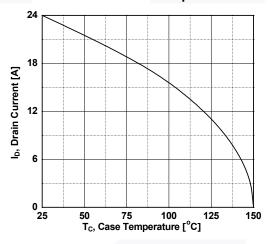
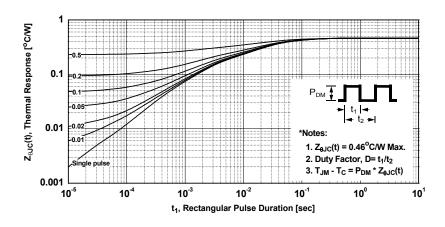


Figure 11. Transient Thermal Response Curve



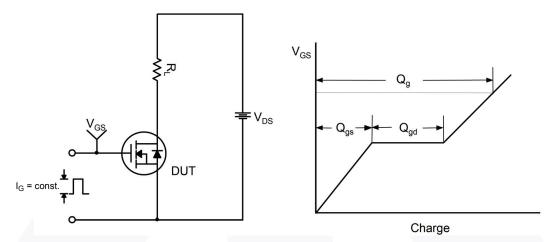


Figure 12. Gate Charge Test Circuit & Waveform

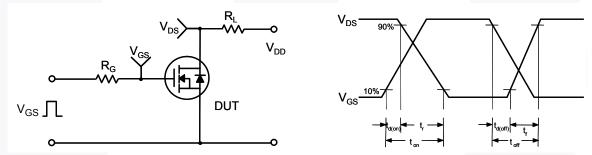


Figure 13. Resistive Switching Test Circuit & Waveforms

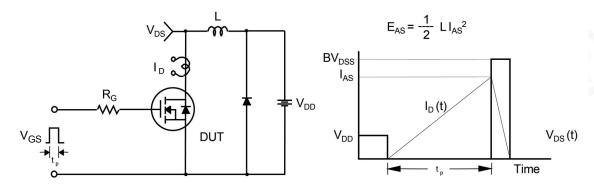


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

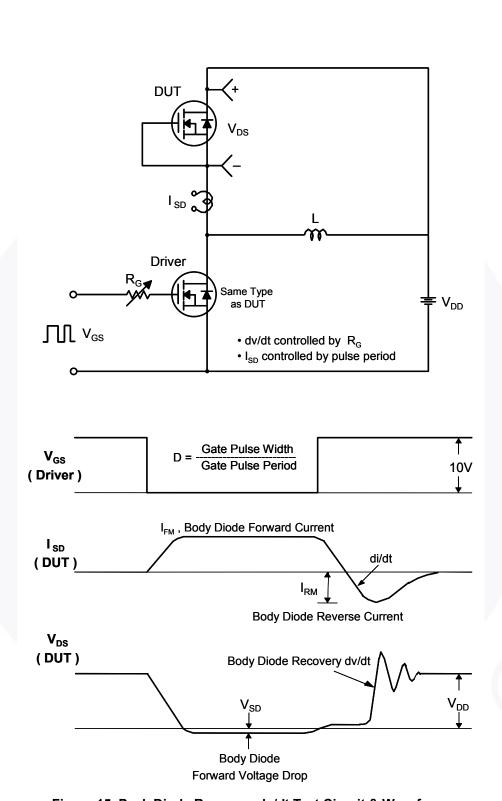
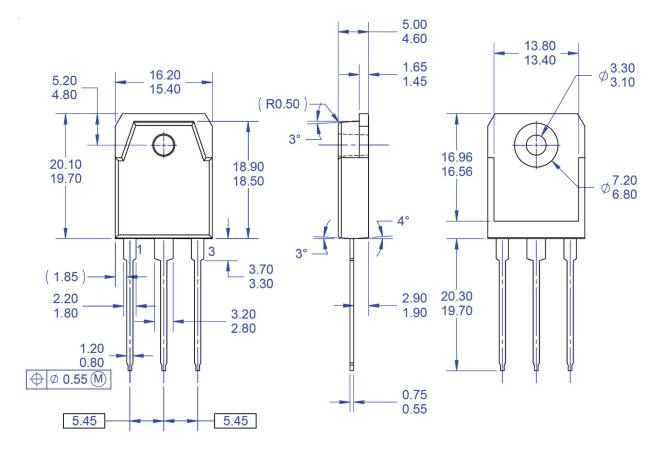
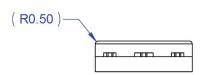


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions





NOTES: UNLESS OTHERWISE SPECIFIED

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- ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSION AND TOLERANCING PER ASME14.5-2009.
- D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS.
 E) DRAWING FILE NAME: TO3PN03AREV1.
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Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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